

Fig. 1a

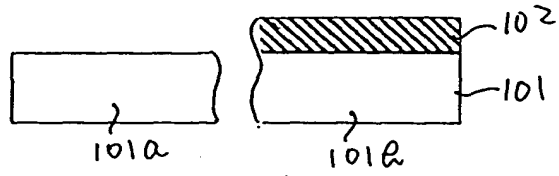


Fig. 1b

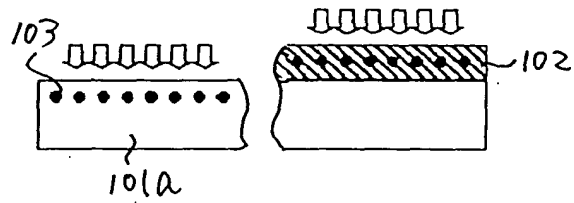


Fig. 1c

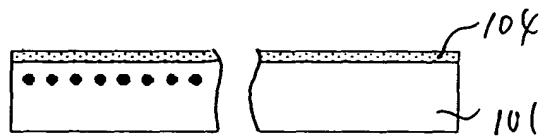


Fig. 1d

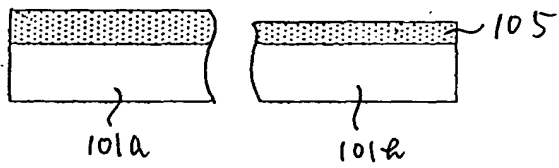


Fig. 1e



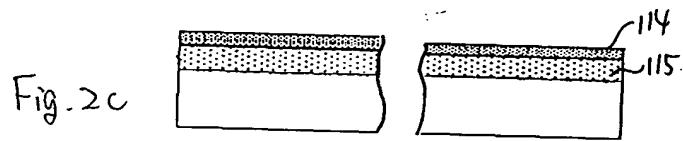
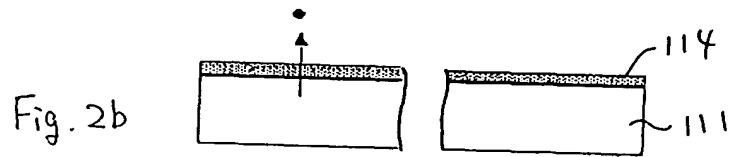
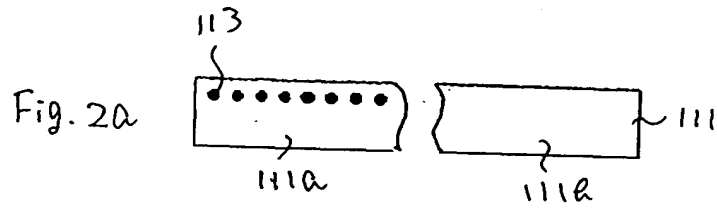


Fig. 3a

1a, 1b, 2

Fig. 3b: A rectangular block 1a with a row of dots on its top surface and a series of vertical rectangular protrusions 3 on top. Cross-section 1b shows a hatched layer 2 with dots on its top surface, resting on block 1.

Fig. 3c: A rectangular block 1a with a row of dots on its top surface and a thin dotted layer 4 on top. Cross-section 1b shows the dotted layer 4 on top of block 1.

Fig. 3d: A rectangular block 1a with a row of dots on its top surface and a thicker dotted layer 5 on top. Cross-section 1b shows the dotted layer 5 on top of block 1.

Fig. 3e: A rectangular block 1a with a row of dots on its top surface and a thick dotted layer 6 on top. Cross-section 1b shows the dotted layer 6 on top of block 1, with a bracket 7 indicating the total thickness of the top layer.

Fig.3e

A cross-sectional view of a semiconductor device. The device consists of a substrate 13 with a layer 14 on top. A layer 16 is formed on layer 14, with two openings 15. In each opening, there is a structure 18. The left structure 18 is labeled 12A and the right one 12R. Each structure 18 has a central part 19 and side parts 20. The side parts 20 are labeled 21A and 21R. The central parts 19 are labeled 22A and 22R. The entire device is labeled 11. Arrows point to the structures 12A and 12R.

TOP SECRET

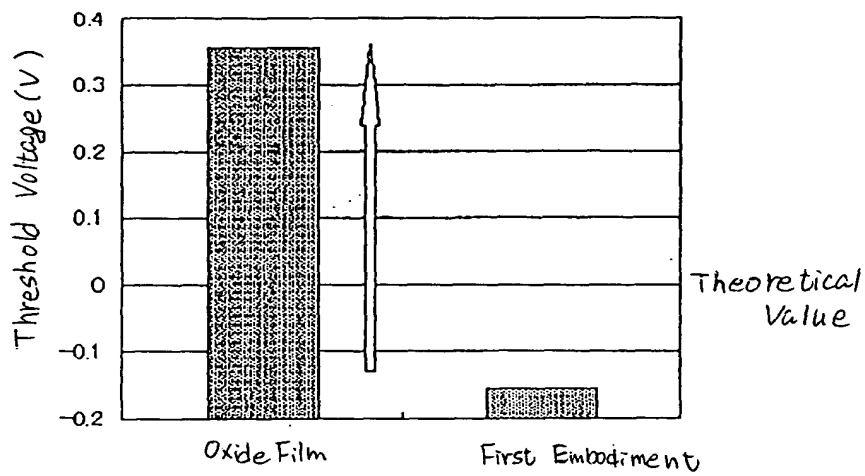


Fig. 6

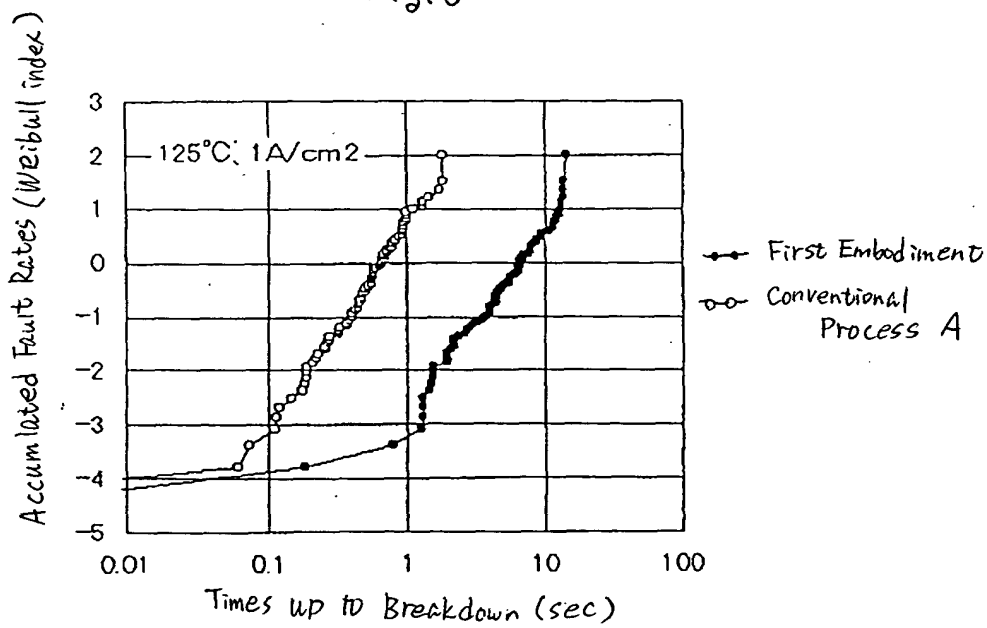


Fig. 7

106T90" E/E8860

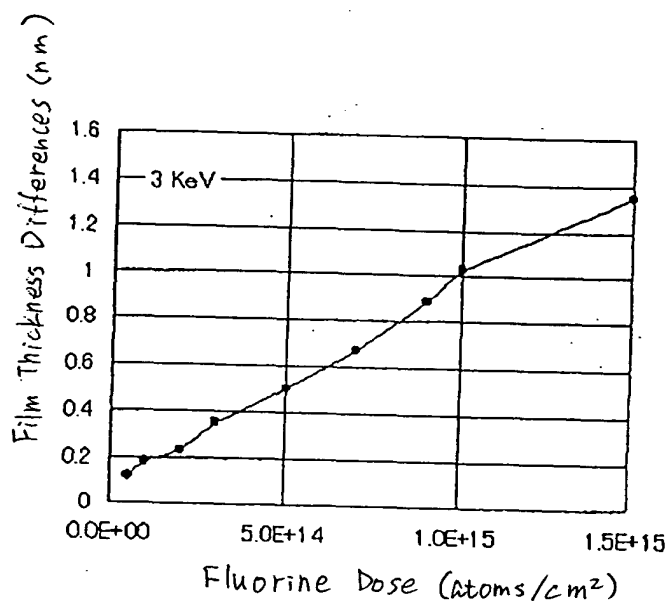


Fig. 8

